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#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Bravo Vasquez and Hill.

Confirmation No.: 9071

Application No.: 09/876,944

Art Unit:

1762

Filed: June 8, 2001

Examiner:

Padgett, Marianne

For:

METHOD FOR THE DEPOSITION

OF MATERIALS FROM

(formerly 8317-120-999)

Attorney Docket No.: 60937-0120

MESOMORPHOUS FILMS

### TRANSMITTAL OF REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' representative encloses herewith a Revocation and Power of Attorney for the above-noted patent application. Applicants' attorney requests that the Power of Attorney be accepted and made of record.

Future correspondence should be forwarded to:

Customer Number 24341

Please note our new docket number, listed above, for future correspondence.

No fee is believed owed with this submission. The Commissioner is authorized to charge any fees associated with this communication to our deposit account number 50-0310. A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 24, 2004

Richard G. A. Bone

Limited Recognition Under 37 C.F.R. § 10.9(b)

(Copy of Certificate attached hereto)

for Victor N. Balancia, Reg. No. 31,231 MORGAN, LEWIS & BOCKIUS LLP

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## REVOCATION AND POWER OF ATTORNEY

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 feb 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

Address:

2520 Barrington Court Hayward, CA 94545



## Schedule A

App.#	Title	Inventor(s)	Filling Date	New Attorney. Docket No.	Former/Attorney
	Compositions for Cleaning Organic				
	and Plasma Etched Residues for				
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing		4.440.040.04	00007.444.110	
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
	Oxalic Acid as a Semiaqueous				,
	Cleaning Product for Copper and		04/04/0000	60937-116-US	8317-116-999
10/421,706	Dielectrics	Lee, et al.	04/24/2003	00937-110-03	0317-110-999
	Sulfoxide Pyrolid(in)one Alkanolamine	7hou of ol	07/12/2002	60937-118-US	8317-118-999
10/193,185	Cleaner Composition	Zhou, et al.	01/12/2002	00937-110-03	0317-110-999
·	Method for the Deposition of Materials				
00/076 044	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
09/876,944	Post Etch Cleaning Composition for	vasquez, et al.	00/00/2001	00007 120 00	0011 120 000
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10/007,134	Photolytic Conversion Process to	1 dyno, or di.	12,0112001		
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
10/200,701	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate			·	
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of				
	Quartz-Coated Polysilicon and Other				
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
,	Cleaning Compositions Containing				
	Hydroxylamine Derivatives and				
	Process Using Same for Residue	71	40/00/000	60027 440 110	9217 140 000
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
	Organisian for Enfallation Agent to				
40/000 040	Composition for Exfoliation Agent to	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
10/689,616	be Used to Remove Resist Residues Reducing Oxide Loss When Using	IVIEIVIII N. Carter	10/22/2003	00901-141-03	0017-141-000
	Fluoride Chemistries to Remove Post-				
	Etch Residues in Semiconductor				
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888
00/407,131	riocessing	Lee, et al.	JUIJEIEUUU	30001 17£-1 1\	172 000

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<u> App.#</u>	SAPARE STATE OF THE SAME OF TH	Minvernor(s)	<u> Dale</u>		DOCKONNO:
10/630,301	Method for Depositing Patterned Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				
	and Silver Oxide Films and Patterned			00007 447 110	0047 447 000
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
	Semiconductor Process Residue	1	06/06/2002	60027 140 116	8317-149-999
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	0317-149-999
	System and Method for Cleaning Workpieces Using Supercritical				
00/400 000	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
60/469,826	Carbon bloxide	r ury, et al.	00/10/2000	00007 100 1 10	0011 100 000
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing			!	
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/000,010					
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
		•			
	Method of Depositing Nanostructured	!			
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of				2247 427 222
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing		00/07/0000	00007 474 110	0247 474 000
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid			,	
40/000 000	Compositions for Cleaning	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
10/688,900	Semiconductor Devices Load Lock System for Supercritical	Daviot, et al.	10/21/2003	00307-172-00	
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/405,900	Automated Dense Phase Fluid	r dry, or di.	00/10/2000		
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
10/100,000	Residue Removers for	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,			
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
	Titanium Carboxylate Films for Use in				
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing				
	Fluoride for Use During		0.4/4.0/0000	00007 405 55	0247 405 000
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing				
00/464 45=	Resists and Manufacturing Method of	ı	04/21/2003	60937-186-PR	8317-186-888
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	00937-100-FR	0017-100-000
10/422 242	Deposition of Permanent Polymer Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999
10/422,212	Structures for OLED Fabrication	Ruman, et al.	0412312003	1 00001-101-00	3017 107-303

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A55 (#)	Title	Inventor(s)	Date .	Docket No.	Docket No.
App.#	Seimconductor Process Residue	<u> </u>	X X		
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,030	Cleaning Compositions and Method of				
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194 <b>-</b> US	8317-194-999
10/000,000	Compositions and Methods for				
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,			•	
	Titanium, Polysilicon, and Other				
	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for	•			
	Polishing Nobel Metal/High K				0047 000 000
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical		40/40/0000	00007 004 DD	0247 204 000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
j l		•			
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing	Carton at al	11/04/2003	60937-206-PR	8317-206-888
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	00937-200-110	0317-200-000
00/404 055	Periodic Acid Compositions for Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
60/494,955	Chemical Mechanical Polishing	Nobell J. Offiair	00/14/2000	00007 207 1 10	0011 201 000
10/692 720	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10/683,730	Alumia Abrasive for Chemical	Oman, ocu.	10/10/200		
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
00/314,020	Moonarioari ellerinig				
	Chemical Mechanical Polishing				
1	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical				0047 040 000
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
	Particulate or Particle-Bound		40/40/0000	60027 047 DE	8317-217-888
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	0317-217-000
	Particulate or Particle-Bound	Cmall at al	10/22/2002	60937-217-US	8317-217-999
10/690,626	Chelating Agents	Small, et al.	10/23/2003	00931-211-03	0011-211-999
	Chemical Mechanical Polishing of STI Features on Semiconductors: Water				
60/522.054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
60/533,054	Pulishing with Oeria Siuries	ru, et al.	12/05/2005	1000. 220 . 10	
	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				
1	Dielectrics Using Superciritcal CO2	,			
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
35.511,045	Method and Apparatus for Substrate				
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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App.#1	Title	Inventor(s)	Filling Date	New Attorney Docket No.	Former Attorney Docket No. 4
60/515.450	Method of Chemically Mechanically Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888

# BEFORE THE OFFICE OF ENROLLMENT AND DISCIPLINE UNITED STATES PATENT AND TRADEMARK OFFICE

## **LIMITED RECOGNITION UNDER 37 CFR § 10.9(b)**

Dr. Richard G. A. Bone is hereby given limited recognition under 37 CFR §10.9(b) as an employee of Morgan, Lewis & Bockius LLP to prepare and prosecute patent applications wherein the patent applicant is the client of Morgan, Lewis & Bockius LLP, and the attorney or agent of record in the applications is a registered practitioner who is a member of Morgan, Lewis & Bockius LLP. This limited recognition shall expire on the date appearing below, or when whichever of the following events first occurs prior to the date appearing below: (i) Dr. Richard G. A. Bone ceases to lawfully reside in the United States, (ii) Dr. Richard G. A. Bone's employment with Morgan, Lewis & Bockius LLP ceases or is terminated, or (iii) Dr. Richard G. A. Bone's current Employment Authorization card expires.

This document constitutes proof of such recognition. The original of this document is on file in the Office of Enrollment and Discipline of the U.S. Patent and Trademark Office.

Expires: November 11, 2004

Harry I. Moatz

Director of Enrollment and Discipline